

ZXMS6008FFQ

60V N-CHANNEL SELF PROTECTED ENHANCEMENT MODE INTELLIFET MOSFET

Product Summary

- Continuous Drain Source Voltage: V_{DS} = 60V
- On-State Resistance: 700mΩ
- Nominal Load Current (VIN = 5V): 1.1A
- Clamping Energy: 90mJ

Description

The DIODES™ ZXMS6008FFQ is a self-protected low-side IntelliFET[®] MOSFET with logic level input. It integrates overtemperature, overcurrent, overvoltage (active clamp), and ESD-protected logic level functionality. The ZXMS6008FFQ is ideal as a general purpose switch driven from 3.3V or 5V microcontrollers in harsh environments where standard MOSFETs are not rugged enough.

Applications

- Especially suited for loads with a high inrush current, such as lamps and motors
- All types of resistive, inductive and capacitive loads in switching applications
- μ C compatible power switches for 12V and 24V DC applications
- Automotive rated
- Replaces electromechanical relays and discrete circuits
- Linear mode capability: the current-limiting protection circuitry is designed to deactivate at low V_{DS} to minimize on-state power dissipation. The maximum DC operating current is therefore determined by the thermal capability of the package/board combination, rather than by the protection circuitry. This does not compromise the product's ability to self-protect at low V_{DS}.

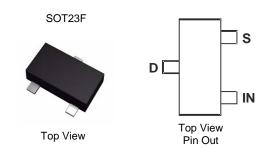
Features and Benefits

- Compact High Power Dissipation Package
- Low Input Current
- Logic Level Input (3.3V and 5V)
- Short Circuit Protection with Auto Restart
- Overvoltage Protection (Active Clamp)
- Thermal Shutdown with Auto Restart
- Overcurrent Protection
- Input Protection (ESD)
- High Continuous Current Rating
- Lead-Free Finish; RoHS Compliant (Note 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The ZXMS6008FFQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: SOT23F
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish @3
- Weight: 0.012 grams (Approximate)



Ordering Information (Note 4)

Part Number	Package Marking		Reel Size (inches)	Tape Width (mm)	Packing	
Fait Nulliber	гаскауе	Warking	Reel Size (inches)	rape width (mm)	Qty.	Carrier
ZXMS6008FFQ-7	SOT23F	1K8	7	8	3,000	Reel

Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

 See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

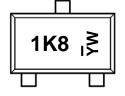
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

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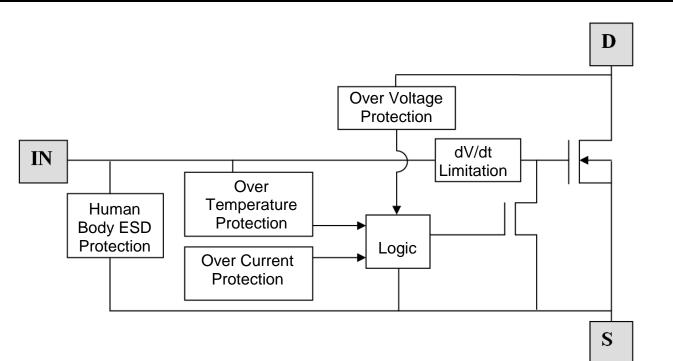


Marking Information



1K8 <u>=</u> Product Type Marking Code Y or Y: Year: 0 to 9 W or W: Week: A-Z: 1 to 26 a-z: 27 to 52 z: Represents 52 & 53 Week

Functional Block Diagram





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Continuous Drain-Source Voltage	Vds	60	V
Drain-Source Voltage for Short Circuit Protection	V _{DS(SC)}	36	V
Continuous Input Voltage	V _{IN}	-0.5 to +6	V
Continuous Input Current @-0.2V \leq V _{IN} \leq 6V Continuous Input Current @V _{IN} $<$ -0.2V or V _{IN} $>$ 6V	lin	No Limit I _{IN} ≤2	mA
Pulsed Drain Current @VIN = 3.3V	I _{DM}	1.4	A
Pulsed Drain Current @V _{IN} = 5V	I _{DM}	1.8	A
Continuous Source Current (Body Diode) (Note 5)	ls	0.7	А
Pulsed Source Current (Body Diode)	lsм	4	А
Unclamped Single Pulse Inductive Energy, $T_J = +25^{\circ}C$, $I_D = 0.5A$, $V_{DD} = 24V$	Eas	90	mJ
Electrostatic Discharge (Human Body Model)	V _{ESD}	4000	V
Charged Device Model	V _{CDM}	1000	V

Thermal Resistance

Characteristic	Symbol	Value	Unit
Power Dissipation at $T_A = +25^{\circ}C$ (Note 5) Linear Derating Factor	PD	0.81 6.54	W mW/°C
Power Dissipation at $T_A = +25^{\circ}C$ (Note 6) Linear Derating Factor	PD	1.5 12	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	Reja	153	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	83	°C/W
Thermal Resistance, Junction to Lead (Note 7)	R _{θJC}	65	°C/W
Operating Temperature Range	TJ	-40 to +150	°C
Storage Temperature Range	Tstg	-55 to +150	°C

 For a device surface mounted on 15mm x 15mm single sided 1oz weight copper on 1.6mm FR-4 board, in still air conditions.
For a device surface mounted on 50mm x 50mm single sided 2oz weight copper on 1.6mm FR-4 board, in still air conditions.
Thermal resistance between junction and the mounting surfaces of drain and source pins. Notes:

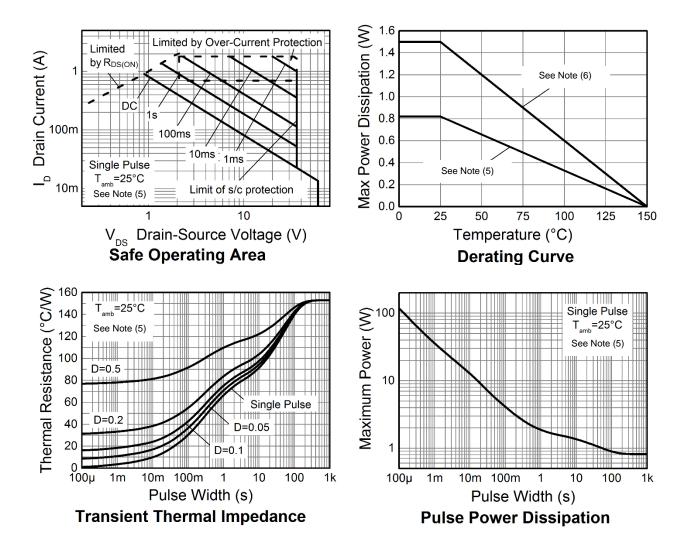
Recommended Operating Conditions

The ZXMS6008FFQ is optimized for use with μC operating from 3.3V and 5V supplies.

Characteristic	Symbol	Min	Max	Unit
Input Voltage Range	VIN	0	5.5	V
Ambient Temperature Range	T _A	-40	+125	°C
High Level Input Voltage for MOSFET to be On	VIH	3	5.5	V
Low Level Input Voltage for MOSFET to be Off	VIL	0	0.7	V
Peripheral Supply Voltage (Voltage to Which Load is Referred)	VP	0	36	V



Thermal Characteristics



Notes: 5. For a device surface mounted on 15mm x 15mm single sided 1oz weight copper on 1.6mm FR-4 board, in still air conditions. 6. For a device surface mounted on 50mm x 50mm single sided 2oz weight copper on 1.6mm FR-4 board, in still air conditions.



Electrical Characteristics (@T_A = +25°C, unless otherwise stated.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Static Characteristics						1
Drain-Source Clamp Voltage	VDS(AZ)	60	65	70	V	I _D = 10mA
Off Olista Dasia Original				0.5	μA	$V_{DS} = 12V, V_{IN} = 0V$
Off State Drain Current	IDSS			1		$V_{DS} = 36V, V_{IN} = 0V$
Input Threshold Voltage	VIN(TH)	0.7	1.2	1.5	V	VDS = VGS, ID = 1mA
Innuit Current		_	60	100		V _{IN} = 3V
Input Current	lin	_	120	200	μA	VIN = 5V
Input Current While Over Temperature Active	_		_	350	μA	VIN = 5V
Statia Duain Courses On State Desistance	5		550	800		V _{IN} = 3V, I _D = 0.5A
Static Drain-Source On-State Resistance	R _{DS(ON)}		500	700	mΩ	V _{IN} = 5V, I _D = 0.5A
Continuous Drain Current (Note E)		0.6		_		VIN = 3V, TA = +25°C
Continuous Drain Current (Note 5)		0.7		_	A	VIN = 5V, TA = +25°C
Continuous Droin Current (Note 6)	- I _D	0.8	—	—		VIN = 3V, TA = +25°C
Continuous Drain Current (Note 6)		0.9	—	—		$V_{IN} = 5V, T_A = +25^{\circ}C$
Current Limit (Note 9)		0.5	1.2	_	A	$V_{IN} = 3V$
Current Limit (Note 8)	ID(LIM)	0.7	1.6	_		VIN = 5V
Dynamic Characteristics						
Turn-On Delay Time	td(on)		5	_	-	V _{DD} = 12V, I _D = 0.5A,
Rise Time	tR	_	10	_		
Turn-Off Delay Time	tD(OFF)	_	45	_	μs	VGS = 5V
Fall Time	tF	_	15	_]	
Overtemperature Protection	·		•		·	
Thermal Overload Trip Temperature (Note 9)	TJT	+150	+175	_	°C	_
Thermal Hysteresis (Note 9)	_		+10	_	°C	

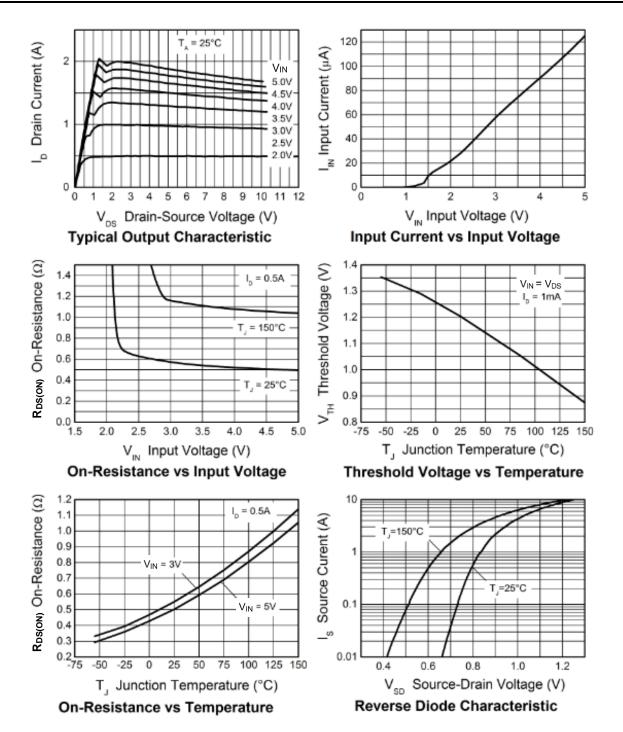
Notes:

 For a device surface mounted on 15mm x 15mm single sided 1oz weight copper on 1.6mm FR-4 board, in still air conditions.
For a device surface mounted on 50mm x 50mm single sided 2oz weight copper on 1.6mm FR-4 board, in still air conditions.
The drain current is restricted only when the device is in saturation (see graph 'Typical Output Characteristic'). This allows the device to be used in the fully on state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside not still are output to a current limit. saturation makes current limit unnecessary.

9. Overtemperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand overtemperature for extended periods.

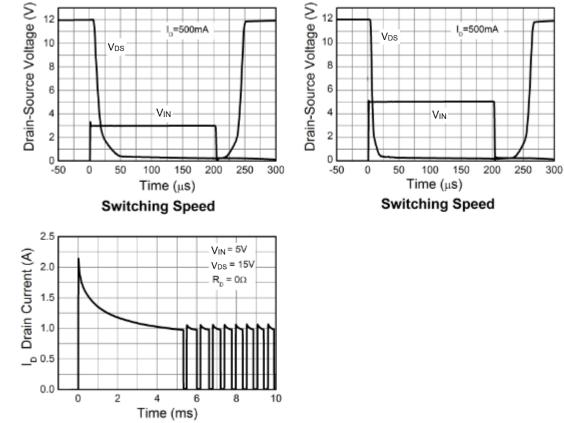


Typical Characteristics





Typical Characteristics (continued)

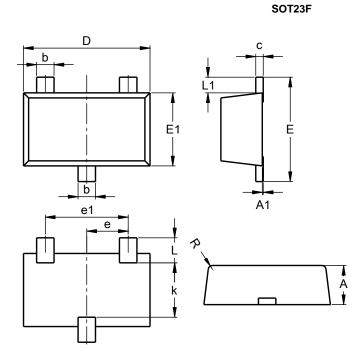


Typical Short Circuit Protection



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

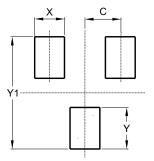


SOT23F					
Dim	Min	Max	Тур		
Α	0.80	1.00	0.90		
A1	0.00	0.10	0.01		
b	0.35	0.50	0.44		
С	0.10	0.20	0.16		
D	2.80	3.00	2.90		
е	0.95 REF				
e1	1.90 REF				
Е	2.30	2.50	2.40		
E1	1.50	1.70	1.65		
k	1.20	-	-		
L	0.30	0.65	0.50		
L1	0.30	0.50	0.40		
R	0.05	0.15	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23F



Dimensions	Value		
Dimensions	(in mm)		
С	0.95		
Х	0.80		
Y	1.110		
Y1	3.000		



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